FORM PTO-1449 U.S. Department of Commerce Patent and Trademark Office LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)	Attorney Docket Number 5649-839CT	Serial No. 10/685,116
	Applicants: Bae et al.	
	Filing Date: October 14, 2003	Group 2811

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U. S. PATENT DOCUMENTS

Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation Yes | No
DWO	1.	WO 97/23000	06/26/97	PCT	H01L29	78	
DWO	2.	JP 9-321307	02/24/03	Japan	H01L29	786	No
DWO	3.	JP 9-321307 Abstract	02/24/03	Japan	H01L29	786	Yes

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

DWO	4.	Alieu et al., "Multiple SiGe well: a new channel architecture for improving both NMOS and PMOS performances," 2000 Symposium on VLSI Technology Digest of Technical Papers, pp. 130-131
DWO	5.	Mizuno et al., "High Performance Strained-Si p-MOSFETs on SiGe-on-Insulator Substrates Fabricated by SIMOX Technology," 1999 IEEE, IEDM, pp. 934-936
DWO	6.	"Sim et al., "Elimination of Parasitic Bipolar-Induced Breakdown Effects in Ultra-Thin SOI MOSFET's Using Narrow-Bandgap-Source (NBS) Structure," IEEE Transactions on Electron Devices, Vol., 42, No. 8, August 1995, pp. 1495-1502
DWO	7.	Yoshimi et al., "Suppression of the Floating-Body Effect in SOI MOSFET's by the Bandgap Engineering Method Using a $Si_{1-\chi}Ge_{\chi}$ Source Structure," IEEE Transactions on Electron Devices, Vol. 44, No. 3, March 1997, pp. 423-429
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EXAMINER Dwight L. Owen DATE CONSIDERED 2/07/05

*EXAMINER Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.